JCT A-650R 12A SCR

Rev.A.1.1

DES PTION:

With ability to withstand the shock loading of larg nt, JCT151A-650R of silicon controlled rect rovides high dV/dt rate with strong resistance to e agnetic interference. It is especially reco ded for use on solid state relay, motorcycle, pow rger, T-tools etc. From all three terminals to exte eatsink,JCT151A-650R provides a rated insu voltage of 2500 $V_{RMS,}$ complying with UL stan (File ref: E252906).
Pac O-220A is RoHS compliant.

MA ATURES

	ol	Value	Unit
	S)	12	A
V	RRM	650	V
		”15	mA

Peak gate current (t_p=20 s , T_j=125)	I_{GM}	4	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D MM				

ORDERING INFORMATION

J	CT	151	A	-650R
JieJie Microelectronics Co., Ltd.	SCRs	$I_{T(RMS)}$:12A	A:TO-220A(Ins)	650R:V_{DRM} /V_{RRM} 1650 V

MARKING

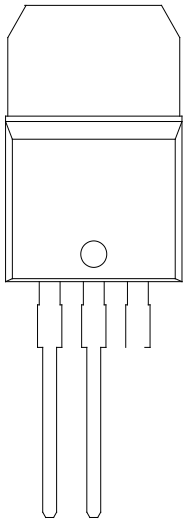


FIG.1: Maximum power dissipation versus RMS on-state current

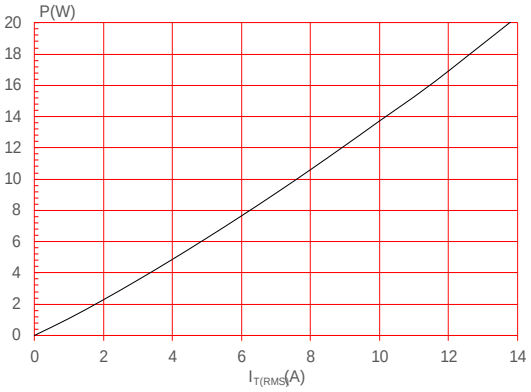
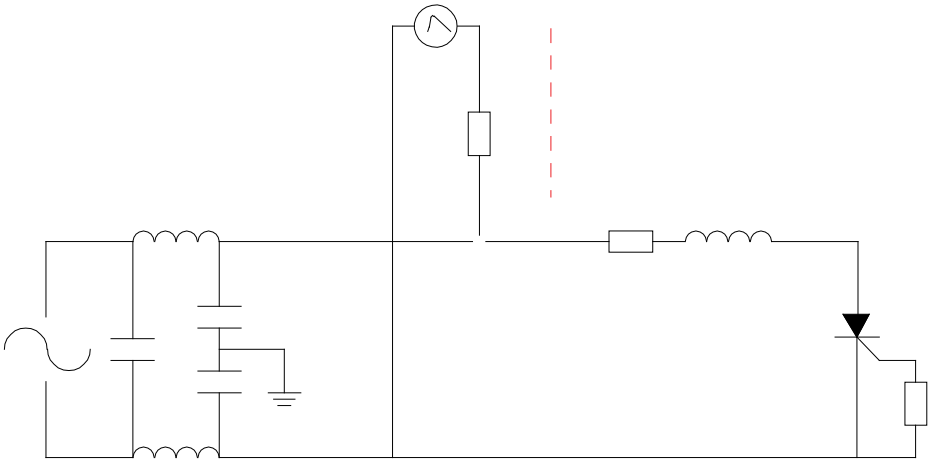


FIG.2: RMS on-state current versus case temperature

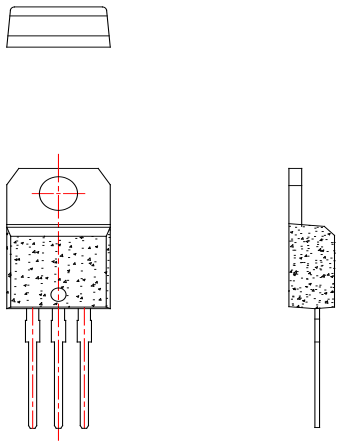
FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT151A-650R	650	15	TO-220A(Ins)	50	Tube

PACKAGE MECHANICAL DATA



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